

SEMITOP[®] 3

3-phase bridge inverter

SK 25 GD 065 ET

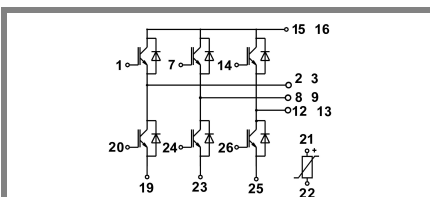
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminum oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL Technology FWD
- Integrated NTC temperature sensor

Typical Applications

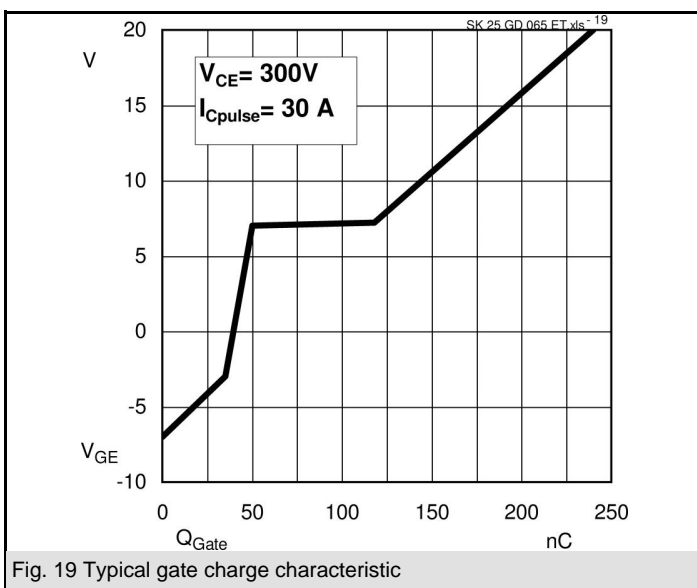
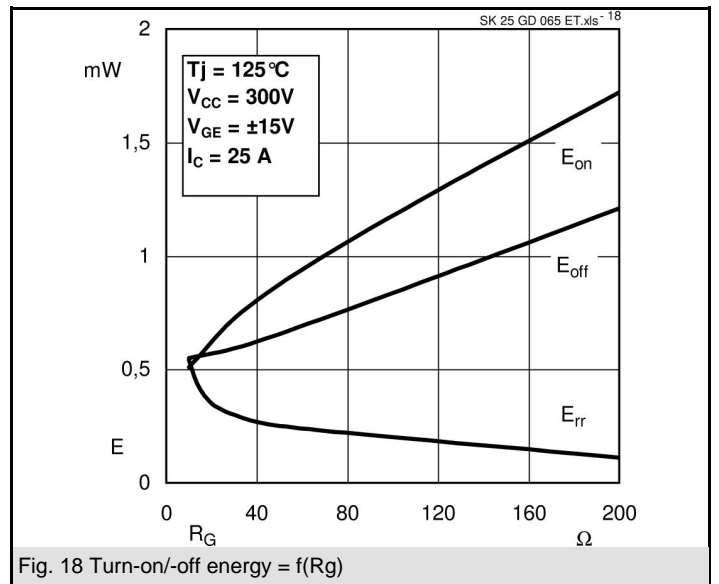
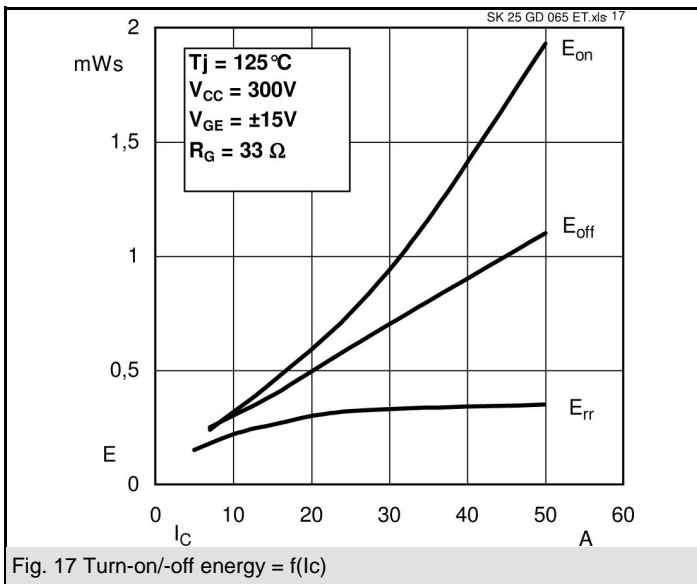
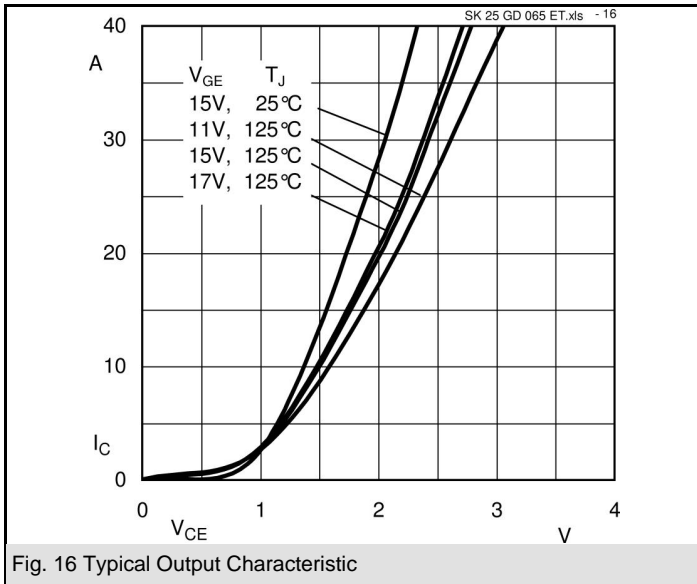
- Inverter

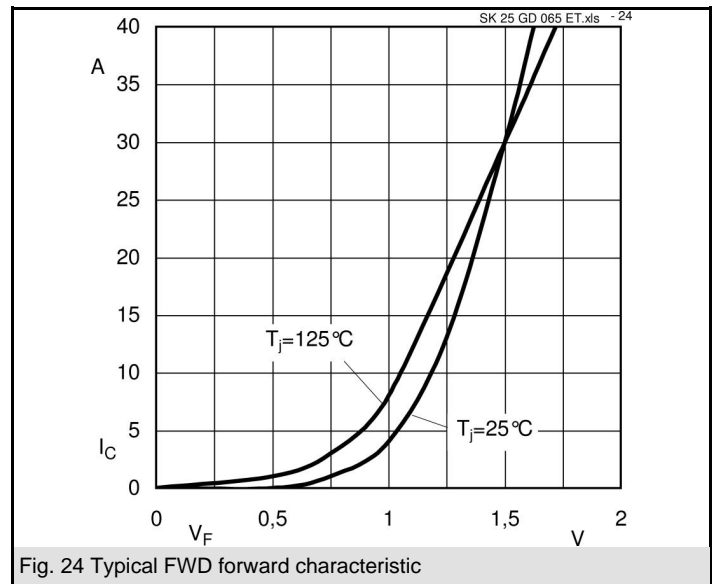
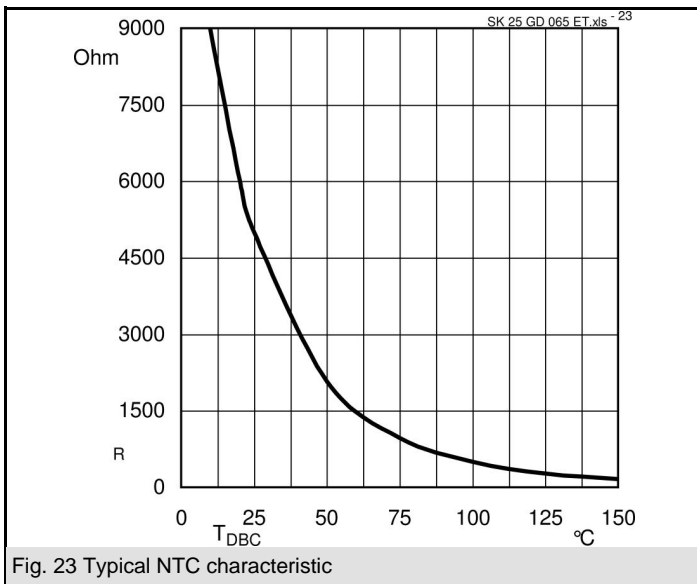
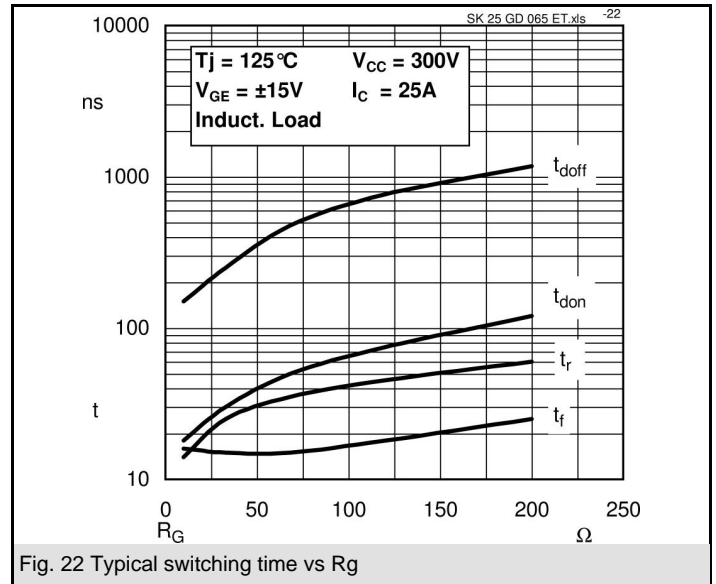
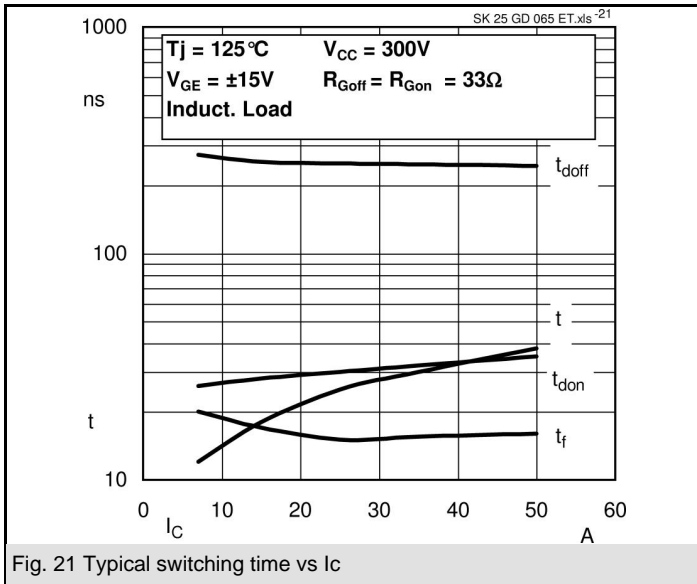


GD - ET

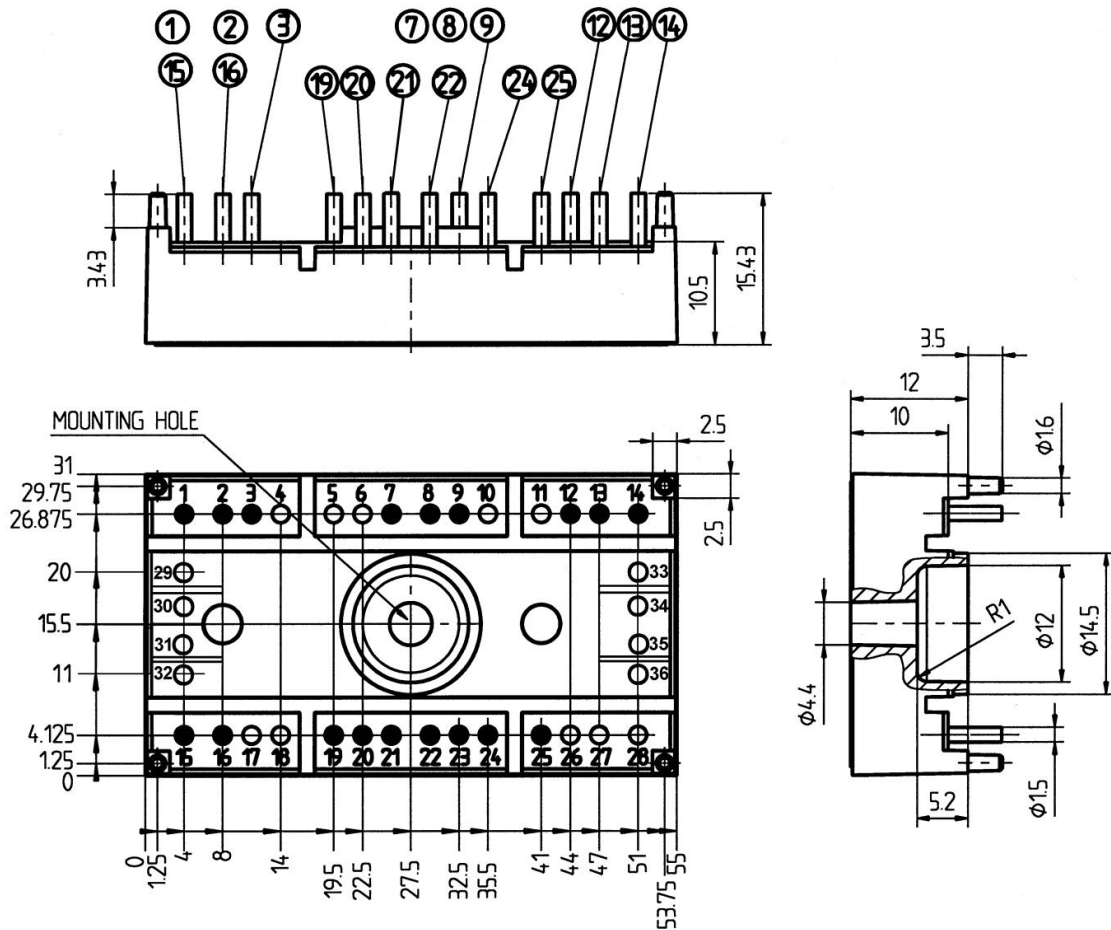
Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	$T_s = 25 (80)^\circ\text{C}$	30 (22)	A
I_{CM}	$T_s = 25 (80)^\circ\text{C}$, $t_p \leq 1 \text{ ms}$	60 (44)	A
V_{GES}		± 20	V
T_j		-40 ... +150	$^\circ\text{C}$
Diode - Inverter, Chopper			
I_F	$T_s = 25 (80)^\circ\text{C}$	36 (24)	A
$I_{FM} = -I_{CM}$	$T_s = 25 (80)^\circ\text{C}$, $t_p \leq 1 \text{ ms}$	72 (48)	A
T_j		-40 ... +150	$^\circ\text{C}$
Rectifier			
V_{RRM}			V
I_{FAV} / I_{TAV}	$T_s = ^\circ\text{C}$		A
I_{FSM} / I_{TSM}	$t_p = \text{ms}$, \sin° , $T_j = ^\circ\text{C}$		A
I_t^2	$t_p = \text{ms}$, \sin° , $T_j = ^\circ\text{C}$		A^2s
T_j			$^\circ\text{C}$
T_{sol}	Terminals, 10s	260	$^\circ\text{C}$
T_{stg}		-40 ... +125	$^\circ\text{C}$
V_{isol}	AC, 1 min. / 1s	2500 / 3000	V

Characteristics		$T_s = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
V_{CEsat}	$I_C = 20 \text{ A}$, $T_j = 25 (125)^\circ\text{C}$		1,8 (2,1)	2 (2,2)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 0,5 \text{ mA}$	3	4	5	V
$V_{CE(TO)}$	$T_j = 25^\circ\text{C}$ (125) $^\circ\text{C}$		1,2 (1,1)	1,3	V
r_T	$T_j = 25^\circ\text{C}$ (125) $^\circ\text{C}$		40 (55)	60	m Ω
C_{ies}	$V_{CE} = 0 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1,6		nF
C_{oes}	$V_{CE} = 0 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		-		nF
C_{res}	$V_{CE} = 0 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		-		nF
$R_{th(j-s)}$	per IGBT			1,4	K/W
$t_{d(on)}$	under following conditions		30		ns
t_r	$V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$		25		ns
$t_{d(off)}$	$I_C = 25 \text{ A}$, $T_j = 125^\circ\text{C}$		250		ns
t_f	$R_{Gon} = R_{Goff} = 33 \Omega$		15		ns
E_{on}	inductive load		0,8		mJ
E_{off}			0,55		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_F = 25 \text{ A}$, $T_j = 25 (125)^\circ\text{C}$		1,45 (1,4)	1,7 (1,75)	V
$V_{(TO)}$	$T_j = 25^\circ\text{C}$ (125) $^\circ\text{C}$		(0,85)	(0,9)	V
r_T	$T_j = 25^\circ\text{C}$ (125) $^\circ\text{C}$		(22)	(32)	m Ω
$R_{th(j-s)}$	per diode			1,7	K/W
I_{RRM}	under following conditions		-		A
Q_{rr}	$I_F = \text{A}$, $V_R = \text{V}$		-		μC
E_{rr}	$V_{GE} = 0 \text{ V}$, $T_j = 125^\circ\text{C}$ $di_F/dt = - \text{A}/\mu\text{s}$		-		mJ
Diode rectifier					
V_F	$I_F = \text{A}$, $T_j = 25^\circ\text{C}$				V
$V_{(TO)}$	$T_j = ^\circ\text{C}$				V
r_T	$T_j = ^\circ\text{C}$				m Ω
$R_{th(j-s)}$	per diode				K/W
Temperatur sensor					
R_{ts}	5 %, $T_r = 25 (100)^\circ\text{C}$		5000(493)		Ω
Mechanical data					
w			30		g
M_s	Mounting torque	2,3		2,5	Nm

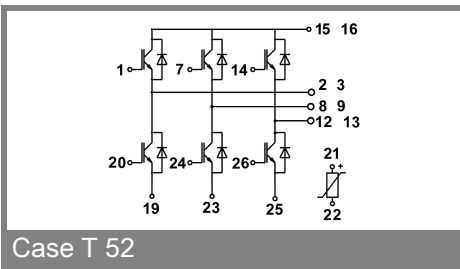




Dimensions in mm



Case T 52 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 52

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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